

In the Claims

Please add the following new independent claims:

32. A method for forming porous silicon oxide film, comprising the steps of:

providing a CVD chamber having inner walls and a wafer chuck/heater;

pre-coating at least a portion of the CVD chamber inner walls with a layer of first PECVD silicon oxide film having a first thermal CVD oxide deposition rate

5 thereupon;

placing a semiconductor wafer on the wafer chuck/heater within pre-coated CVD chamber; the semiconductor wafer including an upper second PECVD silicon oxide film having a second thermal CVD oxide deposition rate thereupon that is less than the first thermal CVD oxide deposition rate upon the first PECVD silicon

10 oxide film coating the CVD chamber inner walls; and

depositing a porous silicon oxide film upon the upper second PECVD silicon oxide film overlying the semiconductor wafer; the porous silicon oxide film being different from the first PECVD silicon oxide film coating the CVD chamber inner walls; whereby the porous silicon oxide film deposits faster upon the first PECVD

15 silicon oxide film than on the upper second PECVD silicon oxide film.

33. A method for forming porous silicon oxide film, comprising the steps of:

providing a CVD chamber having inner walls and a wafer chuck/heater;

pre-coating at least a portion of the CVD chamber inner walls with a layer of first PECVD silicon oxide film having a first thermal CVD oxide deposition rate thereupon;

5 placing a semiconductor wafer on the wafer chuck/heater within pre-coated CVD chamber; the semiconductor wafer including an upper second PECVD silicon oxide film having a second thermal CVD oxide deposition rate thereupon that is less than the first thermal CVD oxide deposition rate upon the first PECVD silicon
10 oxide film coating the CVD chamber inner walls;

pre-heating the semiconductor wafer; and

depositing a porous silicon oxide film upon the upper second PECVD silicon oxide film overlying the semiconductor wafer by a thermal CVD process; the porous silicon oxide film being different from the first PECVD silicon oxide film
15 coating the CVD chamber inner walls; whereby the porous silicon oxide film deposits faster upon the first PECVD silicon oxide film than on the upper second PECVD silicon oxide film.

34. A method for forming porous silicon oxide film, comprising the steps of:

providing a CVD chamber having inner walls and a wafer chuck/heater;

pre-coating at least a portion of the CVD chamber inner walls with a layer of first PECVD silicon oxide film having a first thermal CVD oxide deposition rate
5 thereupon;

placing a semiconductor wafer on the wafer chuck/heater within pre-coated CVD chamber; the semiconductor wafer including an upper second PECVD silicon oxide film having a second thermal CVD oxide deposition rate thereupon that is